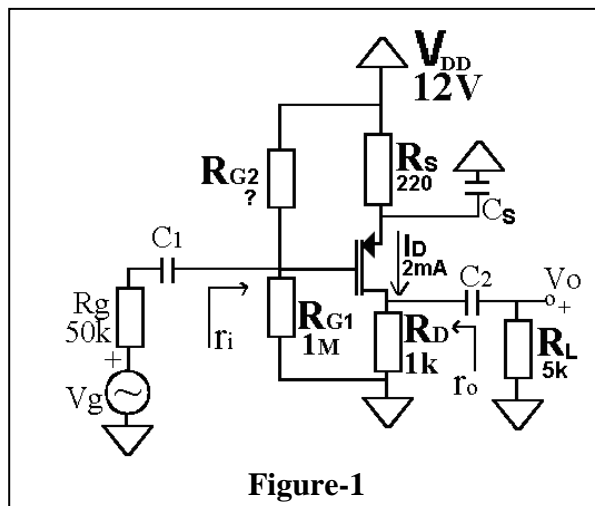


EE232-INTRODUCTION TO ELECTRONICS-FALL 2009
EXERCISE-M4

Q-1- $\beta = 6\text{mA/V}^2$ and $V_t = -1\text{V}$ are given for the MOSFET in Figure-1.

- What should be R_{G2} in order to get $I_D = 2\text{mA}$ in DC case.
- Find the power dissipated on the MOSFET.
- Find the ac input (r_i) and output (r_o) resistances.
- Find the ac gain (V_o/V_i) of the circuit.
- Find the total ac gain (V_o/V_g) of the circuit.



SOLUTION

a)

Source voltage:

$$V_S = V_{DD} - I_D R_S$$

$$V_S = 12 - 2\text{mA} \times 0.22\Omega$$

$$V_S = 11.56\text{V}$$

Gate Voltage:

The transistor is assumed in the saturation region

$$I_D = \frac{\beta}{2} (V_{GS} - V_t)^2$$

$$I_D = \frac{6\text{mA/V}^2}{2} (V_G - V_S - V_t)^2$$

$$I_D = \frac{6\text{mA/V}^2}{2} (V_G - 11.56\text{V} - (-1))^2 = 2\text{mA}$$

$$(V_G - 11.56\text{V} - (-1))^2 = \frac{2}{3}$$

$$(V_G - 11.56\text{V} - (-1)) = -0.82$$

$$V_G = 9.74\text{V}$$

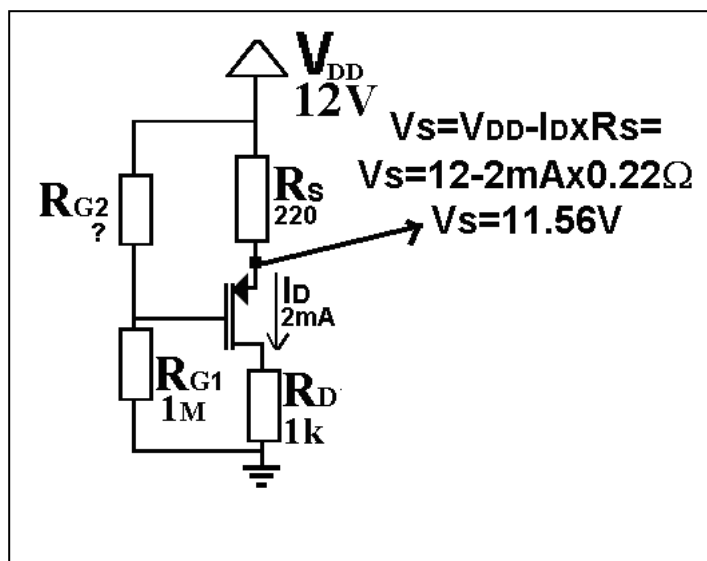
R_{G2} :

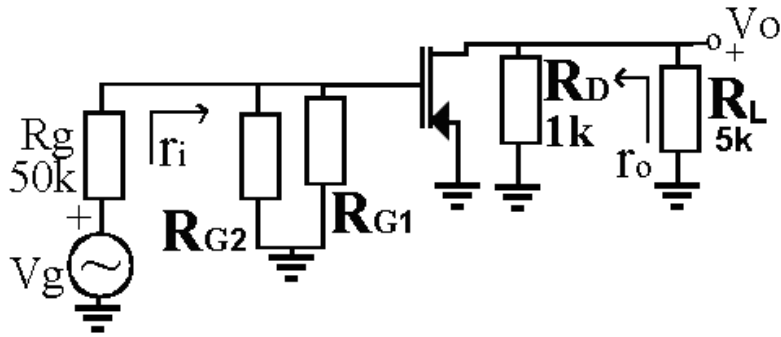
$$V_G = \frac{R_{G1}}{R_{G2} + R_{G1}} V_{DD} = 9.74\text{V} \Rightarrow \frac{R_{G1}}{R_{G2} + R_{G1}} = \frac{9.74\text{V}}{12\text{V}} \Rightarrow R_{G2} \cong 232\text{k}\Omega$$

b)

Dissipated Power on MOSFET:

$$P_{MOS} = I_D \times V_{SD} = 2\text{mA} \times (V_S - V_D) = 2\text{mA} \times (11.56\text{V} - I_D \times R_D) = 2\text{mA} \times 9.56\text{V} = 19.12\text{mW}$$





ac case of the circuit.

c)

input resistance

$$r_i = R_{G1} // R_{G2} = 188k\Omega$$

Note that the input resistance of the MOSFET is infinite.

Output resistance

$$r_o = R_D = 1k$$

Note that V_A is infinite, therefore the ac resistance seen from the drain is infinite.

d)

the gain V_o/V_i

$$\frac{V_o}{V_i} = -\frac{g_m R_d}{1 + g_m R_s} = \frac{-g_m x R_D // R_L}{1 + 0} = -\sqrt{2\beta I_D} x 0.83k\Omega \cong -4.1$$

e)

the gain V_o/V_g

$$\frac{V_o}{V_g} = \frac{V_i}{V_g} \frac{V_o}{V_i} = \frac{R_{G2} // R_{G1}}{R_g + R_{G2} // R_{G1}} x (-4.1) \cong -3.2$$
